

# Silicon Power Schottky Diode

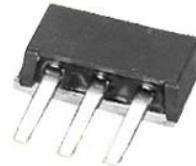
**V<sub>RRM</sub> = 20 V - 100 V**

**I<sub>F</sub> = 80 A**

## Features

- High Surge Capability
- Types up to 100V V<sub>RRM</sub>

**D61-3SM Package**



## Maximum ratings, at T<sub>j</sub> = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	FST8345SM	FST8360SM	FST8380SM	FST83100SM	Unit
Repetitive peak reverse voltage	V <sub>RRM</sub>		45	60	80	100	V
RMS reverse voltage	V <sub>RMS</sub>		32	42	56	70	V
DC blocking voltage	V <sub>DC</sub>		45	60	80	100	V
Continuous forward current	I <sub>F</sub>	T <sub>C</sub> ≤ 110 °C	80	80	80	80	A
Surge non-repetitive forward current, Half Sine Wave	I <sub>F,SM</sub>	T <sub>C</sub> = 25 °C, t <sub>p</sub> = 8.3 ms	800	800	800	800	A
Operating temperature	T <sub>j</sub>		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	T <sub>stg</sub>		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

## Electrical characteristics, at T<sub>j</sub> = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	FST8345SM	FST8360SM	FST8380SM	FST83100SM	Unit
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> = 80 A, T <sub>j</sub> = 25 °C	0.65	0.75	0.84	0.84	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20 V, T <sub>j</sub> = 25 °C	1.5	1.5	1.5	1.5	mA
		V <sub>R</sub> = 20 V, T <sub>j</sub> = 125 °C	500	500	500	500	
<b>Thermal characteristics</b>							
Thermal resistance, junction - case	R <sub>thJC</sub>		1.2	1.2	1.2	1.2	°C/W

